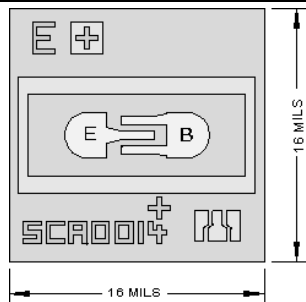


Chip Type 2C4261
Geometry 0014
Polarity PNP

Generic Packaged Parts:
2N4260, 2N4261


[Request Quotation](#)

Chip type **2C4261** by Semicoa Semiconductors provides performance similar to these devices.

Product Summary:

APPLICATIONS:

Designed for low voltage, low gain RF amplifier applications.

Part Numbers:

[2N4261](#), 2N4261UB, 2N4260, 2N4260UB,
 SD4261, SD4261F, SQ4261, SQ4261F

Features: Special Characteristics

$f_t = 1.8 \text{ GHz (typ) at } 10 \text{ mA/10V}$

Mechanical Specifications

Metallization	Top	Al - 12 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	2.1 mils x 2.1 mils
	Base	2.1 mils x 2.1 mils
Die Thickness	8 mils nominal	
Chip Area	16 mils x 16 mils	
Top Surface	Silox Passivated	

Electrical Characteristics

$T_A = 25^\circ\text{C}$

Parameter	Test conditions	Min	Max	Unit
BV_{CEO}	$I_C = 10.0 \text{ mA}, I_B = 0$	15	---	V dc
BV_{CBO}	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	15	---	V dc
BV_{EBO}	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	4.5	---	V dc
h_{FE}	$I_C = 10 \text{ mA dc}, V_{CE} = 1.0 \text{ V dc}$	30	150	---

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 μs , duty cycle less than 2%.